

Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 1350 A



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B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS					
I _{T(AV)} 1350 A					
V _{DRM} /V _{RRM}	400 V, 600 V				
V _{TM}	1.31 V				
I _{GT}	100 mA				
T _J	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1350	А			
I _{T(AV)}	T _{hs}	55	°C			
1		2700	Α			
I _{T(RMS)}	T _{hs}	25	°C			
I _{TSM}	50 Hz	24 400	A			
	60 Hz	25 600	A			
l ² t	50 Hz	2986	kA ² s			
	60 Hz	2726	KA-S			
V _{DRM} /V _{RRM}		400 to 600	V			
t _q	Typical	150	μs			
TJ		-40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
VC CT700C I	04	400	500	80				
VS-ST780CL 06 600		600	700	00				



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current	1	180° condu	ction, half sine v	vave	1350 (500)	Α	
at heatsink temperature	$I_{T(AV)}$	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	2700		
		t = 10 ms	No voltage		24 400	A kA ² s	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		25 600		
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		20 550		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	21 500		
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	2986		
	l ² t	t = 8.3 ms			2726		
Waxiinum i-t for fusing		t = 10 ms			2112		
		t = 8.3 ms	reapplied		1928		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	ms, no voltage	reapplied	29 860	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.80	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$]	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.14	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.13	11122	
Maximum on-state voltage	V_{TM}	$I_{pk} = 3600 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.31	V	
Maximum holding current	Ι _Η	T. = 25 °C	anada supply 1	2 V resistive lead	600	mA	
Typical latching current	IL	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t _q	I_{TM} = 750 A, T_J = T_J maximum, dl/dt = 60 A/μs, V_R = 50 V, dV/dt = 20 V/μs, gate 0 V 100 Ω , t_p = 500 μs	150	μs		

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA			



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PANAMETEN	STIVIBOL	TES	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	, t _p ≤ 5 ms	10.0		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	, f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	, t _p ≤ 5 ms	3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	T. T. marrian at 25 mg			20	
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			5.0	
		T _J = -40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger	200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C		50	-	
		T _J = -40 °C	all units 12 V anode to cathode	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	applied	1.8	3.0	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I_{GD}		Maximum gate	10		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum}$	current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	T _J		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150	30		
Maximum thermal registence, junction to heateigh	В	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031	K/W		
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	0.011	10/00		
waximum thermal resistance, case to heatsink		DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-2	200AC)		

△R _{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TECT COMPITIONS	LIMITO
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum	
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		K/W
60°	0.020	0.020	0.021	0.021		
30°	0.036	0.036	0.036	0.036		

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

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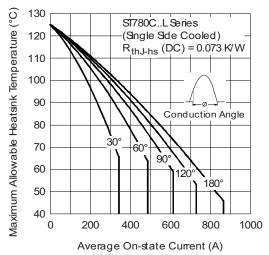


Fig. 1 - Current Ratings Characteristics

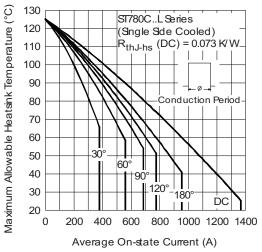


Fig. 2 - Current Ratings Characteristics

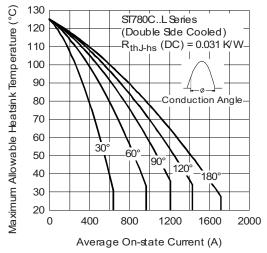


Fig. 3 - Current Ratings Characteristics

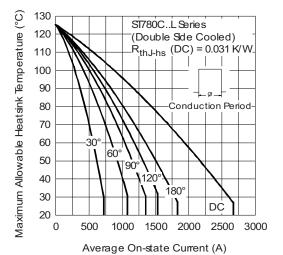


Fig. 4 - Current Ratings Characteristics

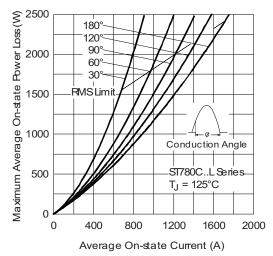


Fig. 5 - On-State Power Loss Characteristics

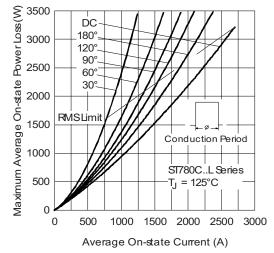
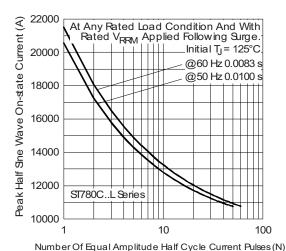


Fig. 6 - On-State Power Loss Characteristics

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Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

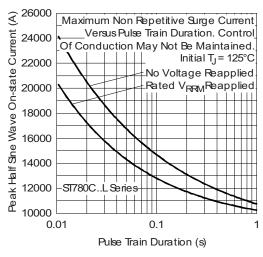


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

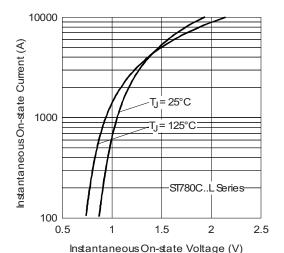


Fig. 9 - On-State Voltage Drop Characteristics

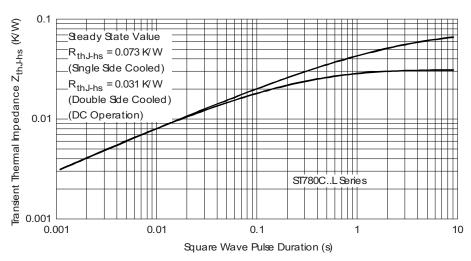


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

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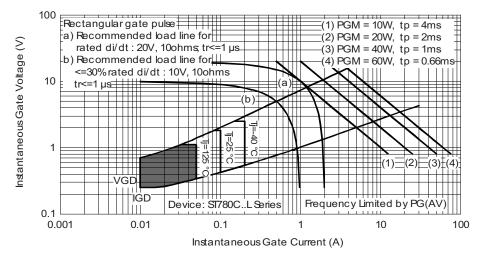
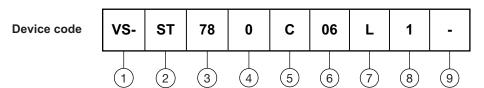


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95076			

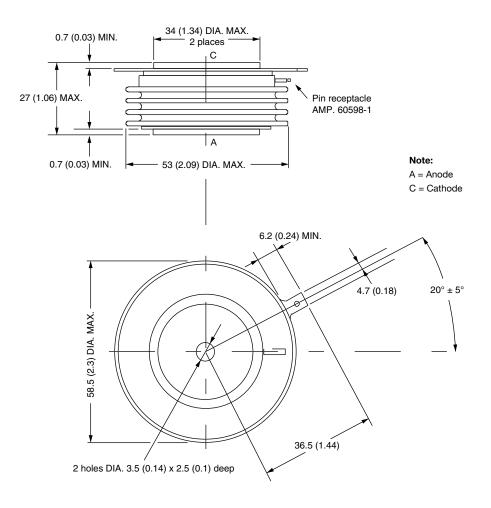


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B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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